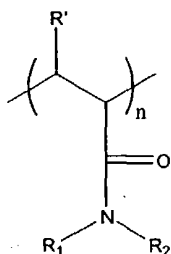


What is claimed is:

1. A photoresist overcoating composition comprising:  
a solvent; and  
a compound represented by Formula 1:

Formula 1



wherein

R' is H or CH<sub>3</sub>;

R<sub>1</sub> and R<sub>2</sub> individually are H or C<sub>1</sub>-C<sub>3</sub> alkyl.

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2. The photoresist overcoating composition according to claim 1,  
wherein the compound of Formula 1 is poly(N,N-dimethylacrylamide).

3. The photoresist overcoating composition according to claim 1,  
15 wherein the solvent is distilled water.

4. The photoresist overcoating composition according to claim 1,  
wherein the compound of Formula 1 is present in an amount ranging from 1 to 30 wt%  
to the solvent.

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5. A process for forming a photoresist pattern, comprises:  
(a) coating a photoresist composition on an underlying layer to form a  
photoresist film;  
(b) coating the photoresist overcoating composition of claim 1 on the  
25 photoresist film to form an overcoating film;  
(c) exposing the resultant structure;  
(d) baking the resultant structure; and  
(e) developing the resultant structure.

6. The process according to claim 5, wherein the photoresist composition includes a chemically amplified photoresist resin.

5 7. The process according to claim 5, wherein the light source of the exposing step is selected from the group consisting of ArF(193 nm), KrF(248 nm), F<sub>2</sub>(157 nm), EUV(13 nm), E-beam, X-ray and ion beam.